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(54) **Title:** PROCESS FOR MANUFACTURING A COMPOSITE SUBSTRATE

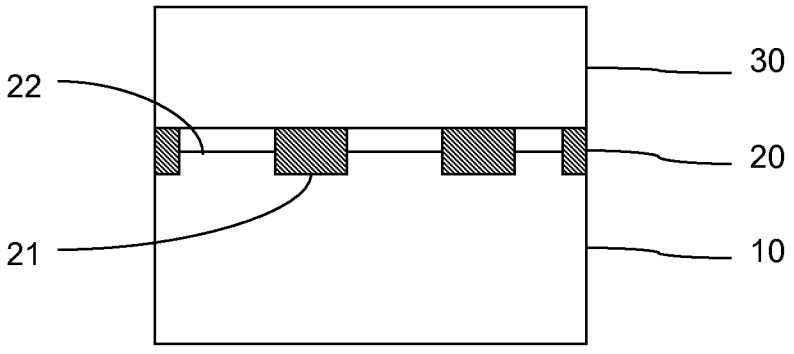



Fig. 1

(57) **Abstract:** The invention relates to a process for manufacturing a composite substrate comprising bonding a first substrate (10) onto a second semi-conducting substrate (30), characterised in that it includes, before bonding, the formation of a bonding layer (20) between the first and the second substrate, said bonding layer (20) comprising a plurality of islands (21) distributed over the surface of the first substrate (10) in a determined pattern and separated from one another by regions (22) of a different type, which are distributed in a complementary pattern, wherein said islands (21) are formed via a plasma treatment of the material of the first substrate (10).

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